

ABSTRACT

There is provided a technique including: forming a first film containing first element and second element; and forming a second film adjacent to the first film and containing the first element and the second element being different in characteristics from the first film, wherein one of the first and second films is formed by performing a first cycle a predetermined number of times, the first cycle including performing: (a1) supplying a first precursor gas containing the first element; and (b1) supplying a first reaction gas containing the second element, and wherein the other of the first and second films is formed by performing a second cycle a predetermined number of times, the second cycle including performing: (a2) supplying a second precursor gas containing the first element and being higher in a thermal decomposition temperature than the first precursor gas; and (b2) supplying a second reaction gas containing the second element.

FIG. 1